



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
40V	17mΩ@10V	15A
	23mΩ@4.5V	

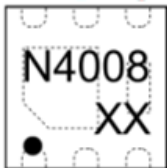
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge

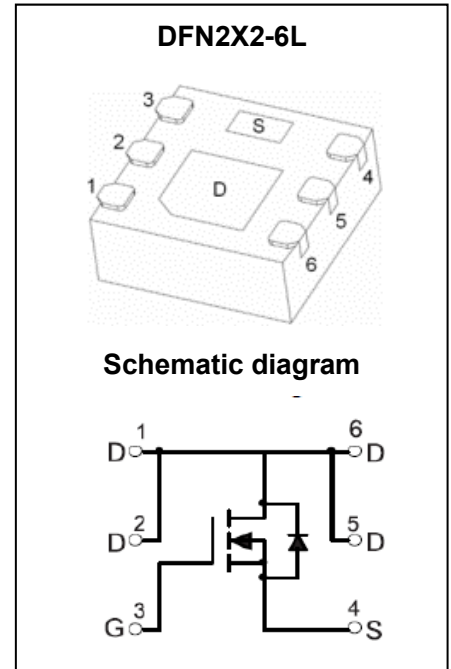
Application

- Load Switch
- DC/DC Converter

MARKING:



N4008 = Device Code
XX = Date Code



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain - Source Voltage	V_{DS}	40	V	
Gate - Source Voltage	V_{GS}	±20	V	
Continuous Drain Current ^{1,5}	$T_C = 25^\circ\text{C}$	I_D	15	A
	$T_C = 100^\circ\text{C}$	I_D	10	A
Pulsed Drain Current ²	I_{DM}	60	A	
Power Dissipation ^{4,5}	$T_A = 25^\circ\text{C}$	P_D	1.8	W
Thermal Resistance from Junction to Ambient ⁵	$R_{\theta JA}$	41	$^\circ\text{C}/\text{W}$	
Thermal Resistance from Junction to Case	$R_{\theta JC}$	16	$^\circ\text{C}/\text{W}$	
Junction Temperature	T_J	150	$^\circ\text{C}$	
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$	

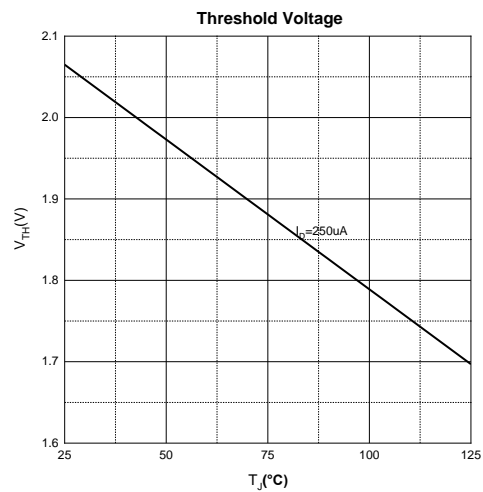
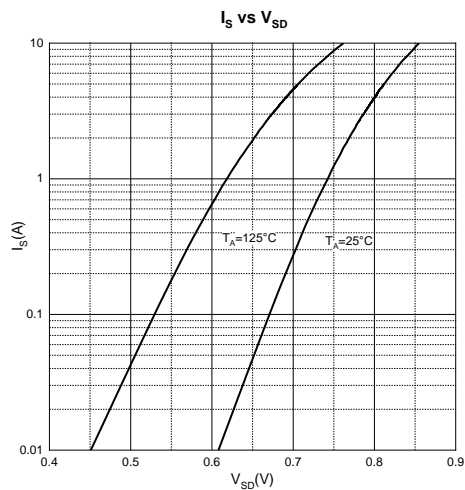
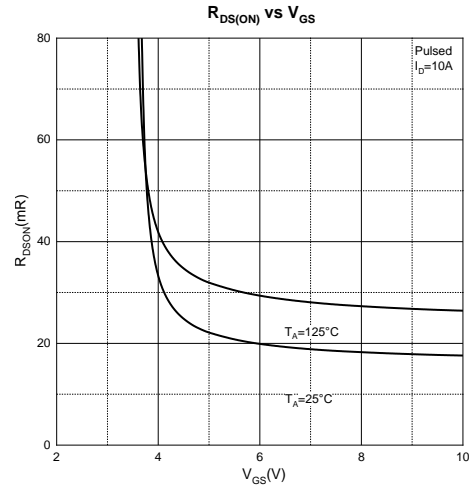
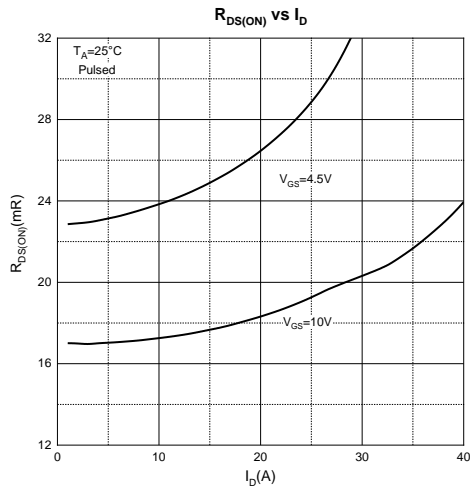
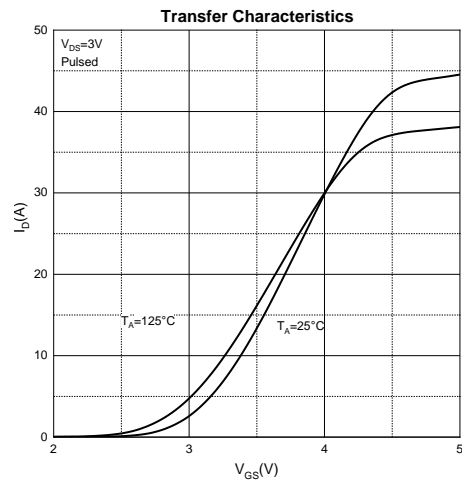
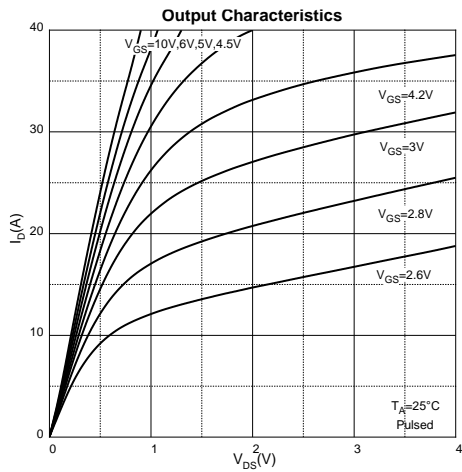
MOSFET ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	40			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40V, V_{GS} = 0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics³						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	2.0	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 8A$		17	22	m Ω
		$V_{GS} = 4.5V, I_D = 8A$		23	29	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 20V, V_{GS} = 0V, f = 1MHz$		712		pF
Output Capacitance	C_{oss}			64		
Reverse Transfer Capacitance	C_{rss}			53		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.8		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 20V, V_{GS} = 10V, I_D = 8A$		14.1		nC
Gate-Source Charge	Q_{gs}			2.3		
Gate-Drain Charge	Q_{gd}			3.4		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15V, V_{GS} = 10V, R_L = 3\Omega, R_G = 3\Omega$		12		ns
Turn-On Rise Time	t_r			3		
Turn-Off Delay Time	$t_{d(off)}$			50		
Turn-Off Fall Time	t_f			5		
Source-Drain Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{GS} = 0V, I_S = 1A$			1.0	V

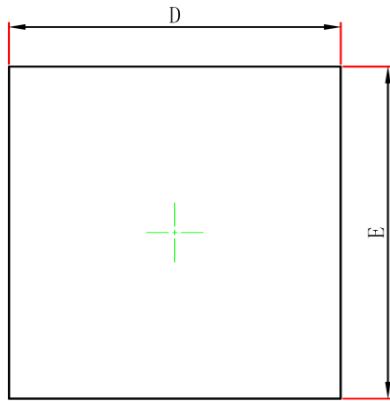
Notes:

1. The maximum current rating is limited by package.
2. Pulse Test: Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
3. Pulse Test: Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.
5. Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

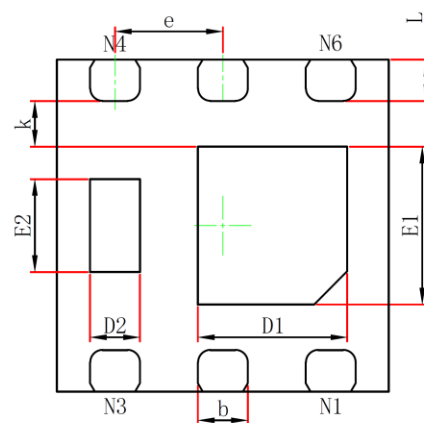
Typical Characteristics



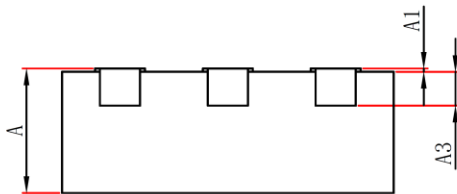
DFN2X2-6L Package Information



TOP VIEW



BOTTOM VIEW



SIDE VIEW

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0	0.050	0	0.002
A3	2.03REF		0.008REF	
D	1.900	2.100	0.075	0.083
E	1.900	2.100	0.075	0.083
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN		0.008MIN	
b	0.250	0.350	0.010	0.014
e	0.65BSC		0.026TYP	
L	0.174	0.326	0.007	0.013

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.